

## SCOPE OF CLAIMS

side of the light to be detected, in the semiconductor substrate.

6. The photodiode array according to any one of Claims 1 to 5,  
wherein a plurality of depressions having a predetermined depth are  
formed in array on the opposite surface side to the incident surface of  
the light to be detected, in the semiconductor substrate, and

wherein each said photodiode is formed in a bottom portion of the associated depression.

7. A method of producing a photodiode array, the method comprising:

10 a step of preparing a semiconductor substrate comprised of a semiconductor of a first conductivity type;

a step of forming a plurality of impurity diffused layers of a second conductivity type on one surface side of the semiconductor substrate to form a plurality of photodiodes each comprised of the impurity diffused layer and the semiconductor substrate, in array; and

20 a step of forming a depression with a predetermined depth more  
depressed than a region not corresponding to regions where the  
photodiodes are formed, in regions corresponding to the regions where  
the photodiodes are formed, on another surface of the semiconductor  
substrate.

8. The method according to Claim 7, further comprising a step of forming a high-impurity-concentration layer of the first conductivity type on the other surface of the semiconductor substrate, after the step of forming the depression.

25 9. A method of producing a photodiode array, the method comprising:

a step of preparing a semiconductor substrate comprised of a semiconductor of a first conductivity type;

5 a step of forming a plurality of first depressions in array on one surface side of the semiconductor substrate;

10 a step of forming a plurality of impurity diffused layers of a second conductivity type in bottom portions of the first depressions to form a plurality of photodiodes each comprised of the impurity diffused layer and the semiconductor substrate, in array; and

15 a step of forming a second depression with a predetermined depth more depressed than a region not corresponding to regions where the photodiodes are formed, in regions corresponding to the regions where the photodiodes are formed, on another surface of the semiconductor substrate.

10. The method according to Claim 9, further comprising a step of forming a high-impurity-concentration layer of the first conductivity type on the other surface of the semiconductor substrate, after the step of forming the second depression.

15 20 25 11. The method according to any one of Claims 7 to 10, further comprising a step of providing an impurity region of the first conductivity type between the impurity diffused layers adjacent to each other.

12. A radiation detector comprising:

the photodiode array as set forth in any one of Claims 1 to 6; and

25 a scintillator panel arranged opposite to the incident surface of the light to be detected in the photodiode array, and arranged to emit

light with incidence of radiation.

13. A radiation detector comprising:

the photodiode array produced by the method as set forth in

Claim 7 or 8; and

5 a scintillator panel arranged opposite to the surface where the depression is formed in the photodiode array, and arranged to emit light with incidence of radiation.

14. A radiation detector comprising:

the photodiode array produced by the method as set forth in

10 Claim 9 or 10; and

a scintillator panel arranged opposite to the surface where the second depression is formed in the photodiode array, and arranged to emit light with incidence of radiation.